

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

TIP101, TIP102, TIP106 and TIP107 are Preferred Devices

Plastic Medium-Power Complementary Silicon Transistors

Designed for general-purpose amplifier and low-speed switching applications.

Features

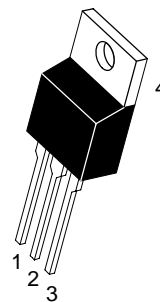
- High DC Current Gain –
 $h_{FE} = 2500$ (Typ) @ I_C
 $= 4.0$ Adc
- Collector–Emitter Sustaining Voltage – @ 30 mAdc
 $V_{CEO(sus)} = 60$ Vdc (Min) – TIP100, TIP105
 $= 80$ Vdc (Min) – TIP101, TIP106
 $= 100$ Vdc (Min) – TIP102, TIP107
- Low Collector–Emitter Saturation Voltage –
 $V_{CE(sat)} = 2.0$ Vdc (Max) @ I_C
 $= 3.0$ Adc
 $= 2.5$ Vdc (Max) @ $I_C = 8.0$ Adc
- Monolithic Construction with Built-in Base–Emitter Shunt Resistors
- Pb–Free Packages are Available*



ON Semiconductor®

<http://onsemi.com>

DARLINGTON 8 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60–80–100 VOLTS, 80 WATTS



MARKING DIAGRAM



TO-220AB
CASE 221A
STYLE 1

TIP10x = Device Code
x = 0, 1, 2, 5, 6, or 7
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

MAXIMUM RATINGS

| Rating | Symbol | TIP100, TIP105 | TIP101, TIP106 | TIP102, TIP107 | Unit |
|---|----------------|-------------------|-------------------|-------------------|--------------------------|
| Collector – Emitter Voltage | V_{CEO} | 60 | 80 | 100 | Vdc |
| Collector – Base Voltage | V_{CB} | 60 | 80 | 100 | Vdc |
| Emitter – Base Voltage | V_{EB} | 5.0 | | | Vdc |
| Collector Current – Continuous – Peak | I_C | 8.0 15 | | | Adc |
| Base Current | I_B | 1.0 | | | Adc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 80 0.64 | | | W W/ $^\circ\text{C}$ |
| Unclamped Inductive Load Energy (1) | E | 30 | | | mJ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 2.0 0.016 | | | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | –65 to +150 | | | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|--------------------|
| Thermal Resistance, Junction–to–Case | $R_{\theta JC}$ | 1.56 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 62.5 | $^\circ\text{C/W}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $I_C = 1.1\text{ A}$, $L = 50\text{ mH}$, P.R.F. = 10 Hz, $V_{CC} = 20\text{ V}$, $R_{BE} = 100\ \Omega$

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|---------------------|-----------------|
| TIP100 | TO–220 | 50 Units / Rail |
| TIP100G | TO–220 (Pb–Free) | 50 Units / Rail |
| TIP101 | TO–220 | 50 Units / Rail |
| TIP101G | TO–220 (Pb–Free) | 50 Units / Rail |
| TIP102 | TO–220 | 50 Units / Rail |
| TIP102G | TO–220 (Pb–Free) | 50 Units / Rail |
| TIP105 | TO–220 | 50 Units / Rail |
| TIP105G | TO–220 (Pb–Free) | 50 Units / Rail |
| TIP106 | TO–220 | 50 Units / Rail |
| TIP106G | TO–220 (Pb–Free) | 50 Units / Rail |
| TIP107 | TO–220 | 50 Units / Rail |
| TIP107G | TO–220 (Pb–Free) | 50 Units / Rail |

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|---------------|-----------------|----------------|---------------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage (1) ($I_C = 30\text{ mA}$, $I_B = 0$) | $V_{CE(sus)}$ | 60 80 100 | – – – | Vdc |
| Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$) | I_{CEO} | – – – | 50 50 50 | μA |
| Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) | I_{CBO} | – – – | 50 50 50 | μA |
| Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | – | 8.0 | mA |
| ON CHARACTERISTICS (1) | | | | |
| DC Current Gain ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 8.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) | h_{FE} | 1000 200 | 20,000 – | – |
| Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ A}$, $I_B = 6.0\text{ mA}$) ($I_C = 8.0\text{ A}$, $I_B = 80\text{ mA}$) | $V_{CE(sat)}$ | – – | 2.0 2.5 | Vdc |
| Base–Emitter On Voltage ($I_C = 8.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) | $V_{BE(on)}$ | – | 2.8 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Small–Signal Current Gain ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ MHz}$) | h_{fe} | 4.0 | – | – |
| Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$) | C_{ob} | – – | 300 200 | pF |

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

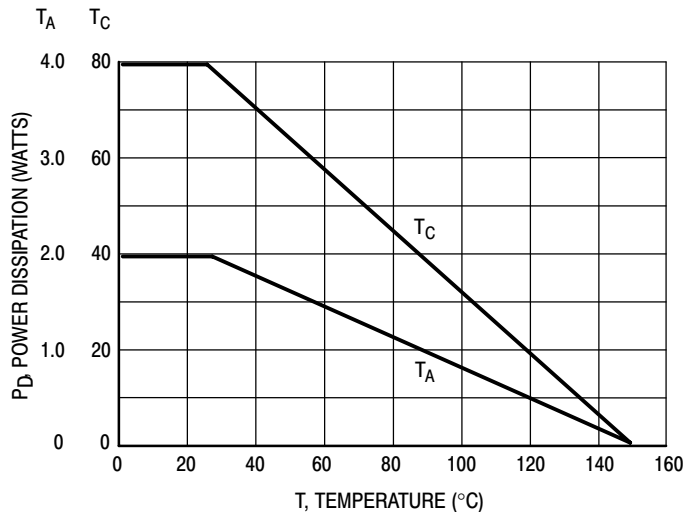


Figure 1. Power Derating

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

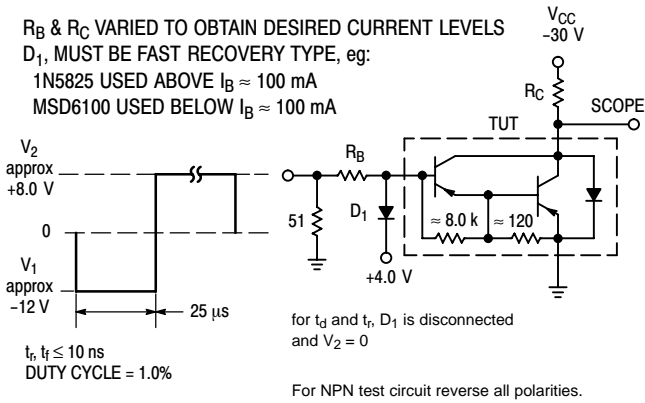


Figure 2. Switching Times Test Circuit

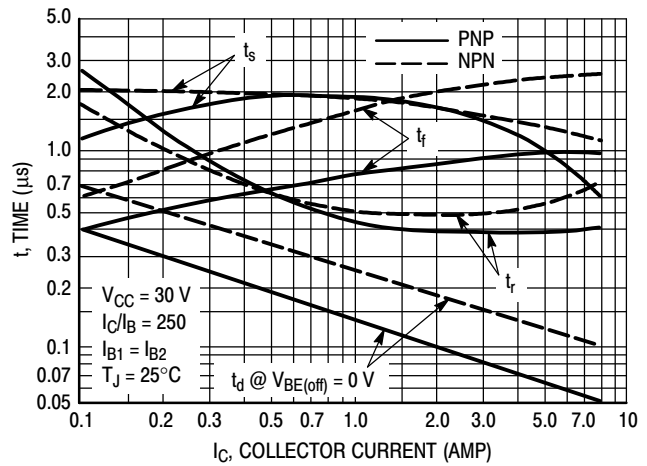


Figure 3. Switching Times

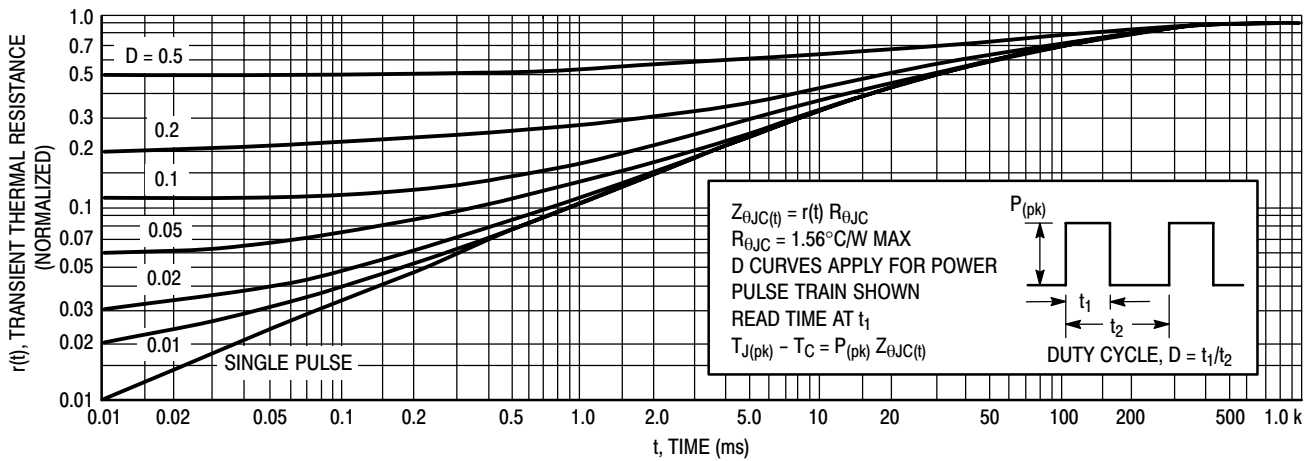


Figure 4. Thermal Response

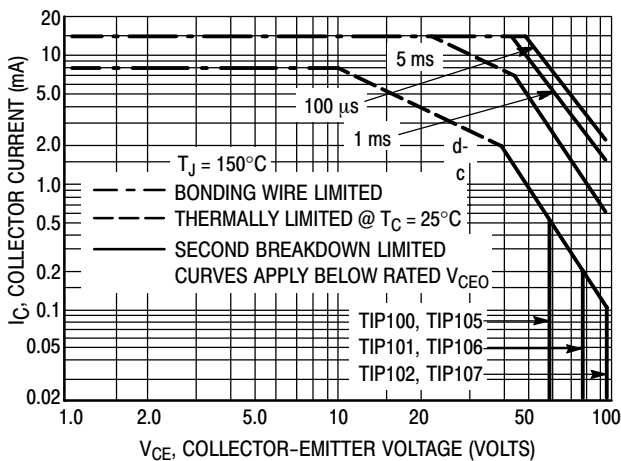


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

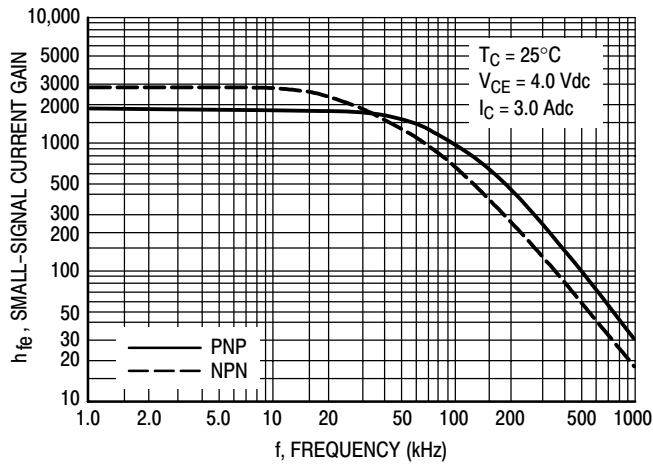


Figure 6. Small-Signal Current Gain

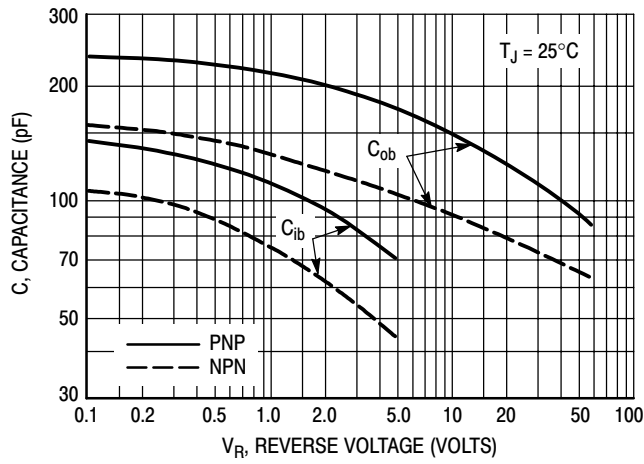


Figure 7. Capacitance

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

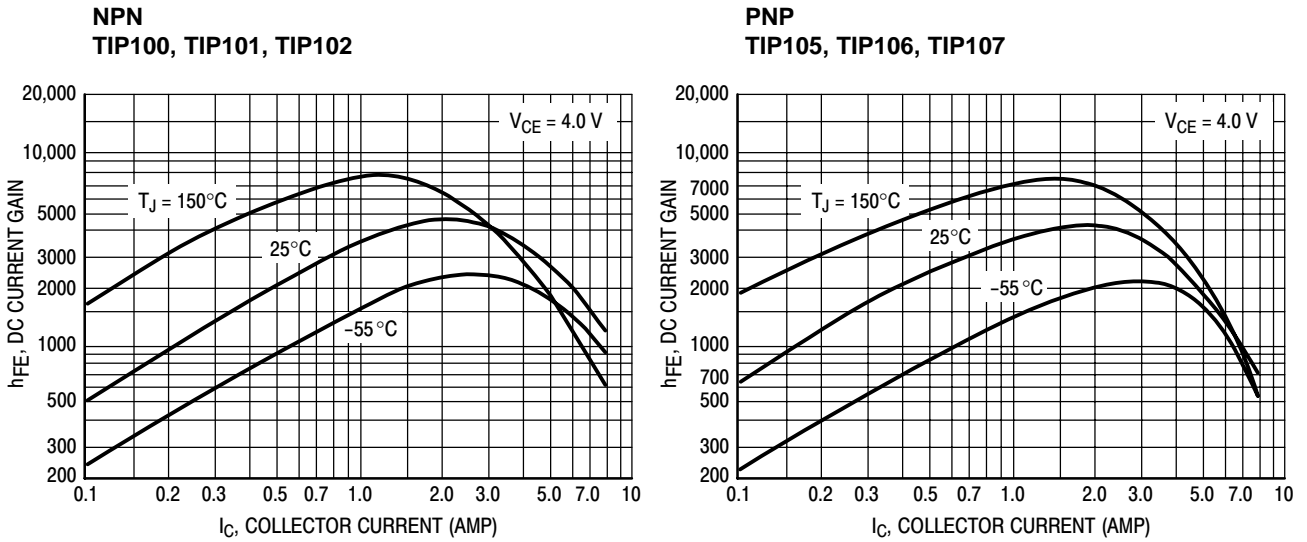


Figure 8. DC Current Gain

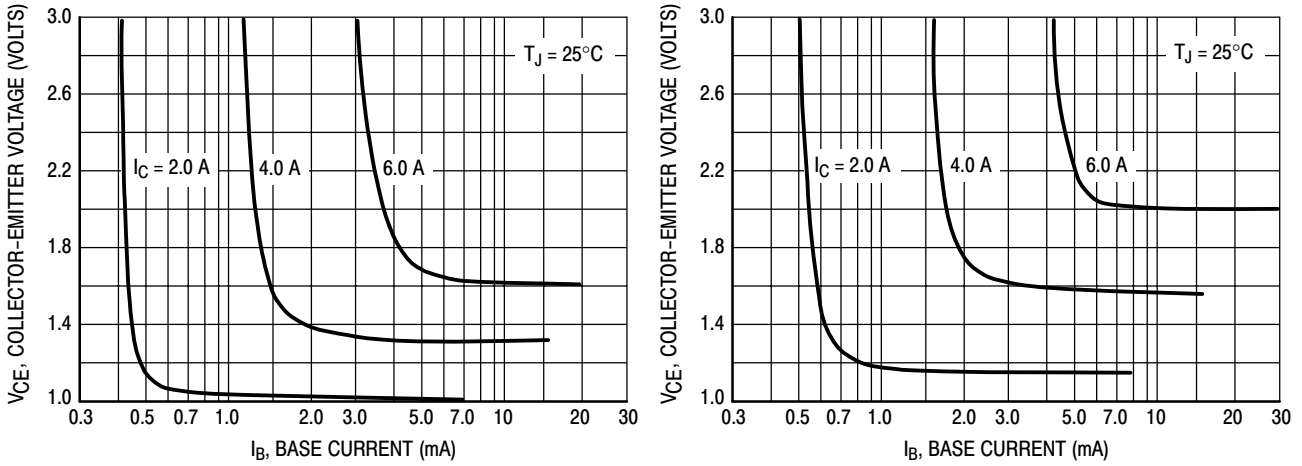


Figure 9. Collector Saturation Region

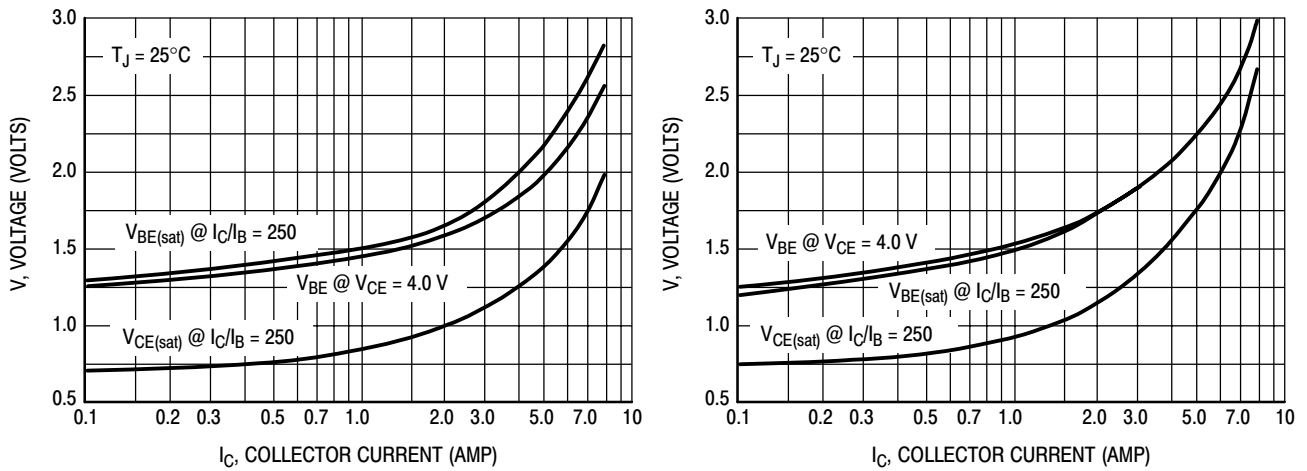
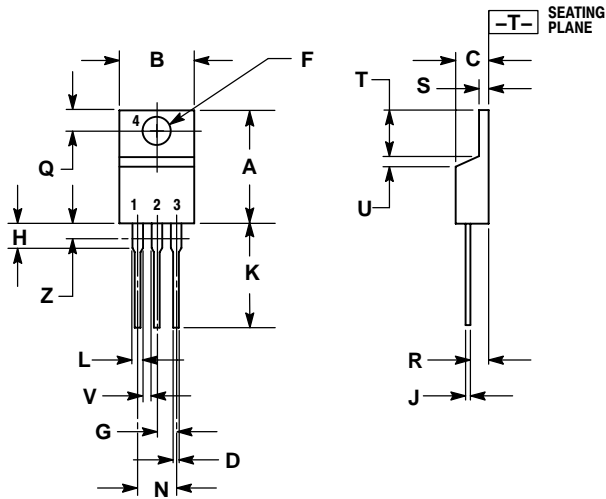


Figure 10. "On" Voltages

TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.